

**TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT**

Under 37 CFR 1.97(b) or 1.97(c)

Docket No.

OKI.227

In Re: Application of Norio HIRASHITA

Serial No.

NEW

Filing Date

APRIL 5, 2001

Examiner

TO BE ASSIGNED

Group Art Unit

TO BE ASSIGNED

Title: A STRUCTURE OF A FIELD EFFECT TRANSISTOR HAVING A METALLIC SILICIDE AND  
MANUFACTURING METHOD THEREOF

Address to:

Assistant Commissioner for Patents  
Washington, D.C. 20231

**37 CFR 1.97(b)**

1. ☒ The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application; within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; or before the mailing date of a first Office Action on the merits, whichever event occurs last.

**37 CFR 1.97(c)**

2. ☐ The Information Disclosure Statement submitted herewith is being filed after three months of the filing of a national application, or the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; or after the mailing date of a first Office Action on the merits, whichever occurred last but before the mailing date of either:

1. a Final Action under 37 CFR 1.113, or
2. a Notice of Allowance under 37 CFR 1.311,

whichever occurs first.

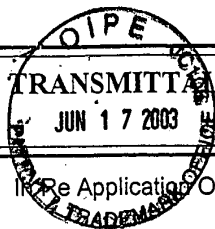
Also submitted herewith is:

- ☐ a certification as specified in 37 CFR 1.97(e);

OR

- ☐ the fee set forth in 37 CFR 1.17(p) for submission of an Information Disclosure Statement under 37 CFR 1.97(c).

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**Payment of Fee**

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

- ☐ A check in the amount of \_\_\_\_\_ is attached.
- ☐ The Assistant Commissioner is hereby authorized to charge and credit Deposit Account No. \_\_\_\_\_ as described below. A duplicate copy of this sheet is enclosed.
- ☐ Charge the amount of \_\_\_\_\_
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Dated: APRIL 5, 2001

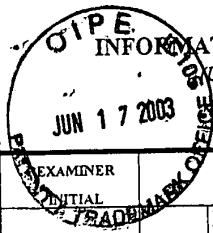
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## INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

OKI.227

Application Number

NEW

Applicant(s)

Norio HIRASHITA et al.

Filing Date

APRIL 5, 2001

Group Art Unit

TO BE ASSIGNED

EXAMINER

INITIAL

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

A

Deep sub-0.1 um MOSFET's with Very Thin SOL Layer for Ultra-Low Power Applicants, Information and Communication Engineers C-II Vol. J81-C-II No. 3, pp. 313-319, August 1998.

B

Optimization of Series Resistance in Sub-0.2 um SOI MOSFET's, IEEE Electron Device letters, VOL. 15, No. 9, September 1994, p. 363-365.

C

Optimization of series resistance in Sub-0.2 um SOI MOSFET's, 1993 IEEE, pp. IEDM93-723-726-IEDM 93.

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EXAMINER

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\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.